

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED PLANAR TYPE

**2SC4686, 2SC4686A**

TV DYNAMIC FOCUS APPLICATIONS

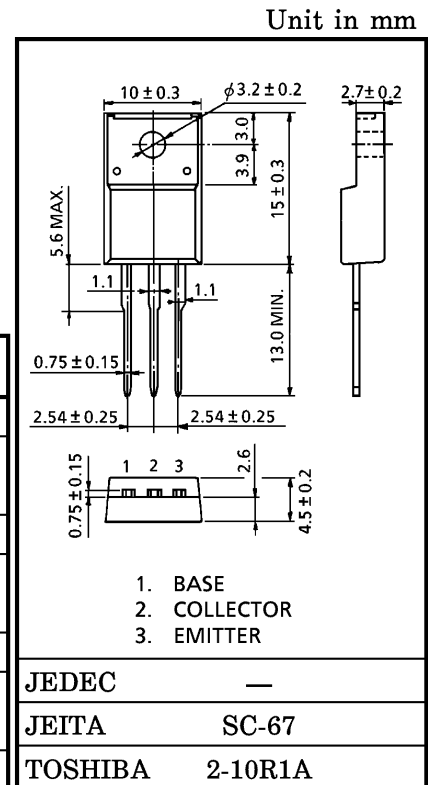
HIGH VOLTAGE SWITCHING APPLICATIONS

HIGH VOLTAGE AMPLIFIER APPLICATIONS

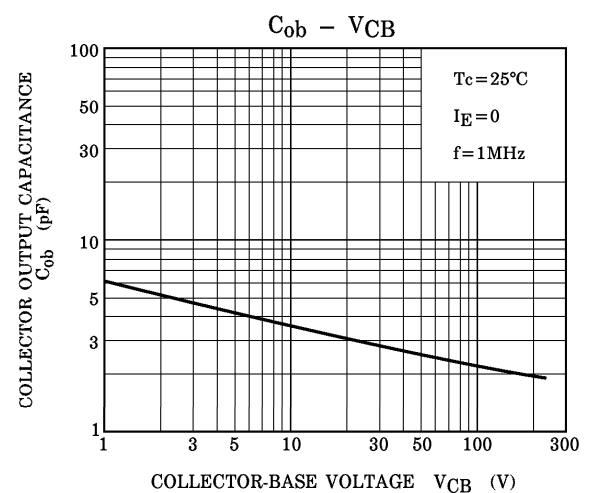
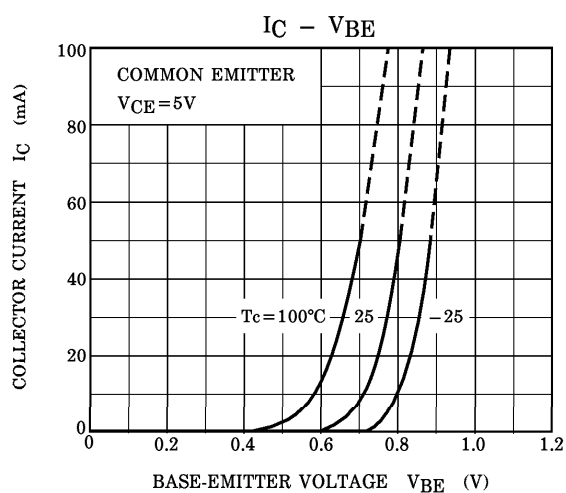
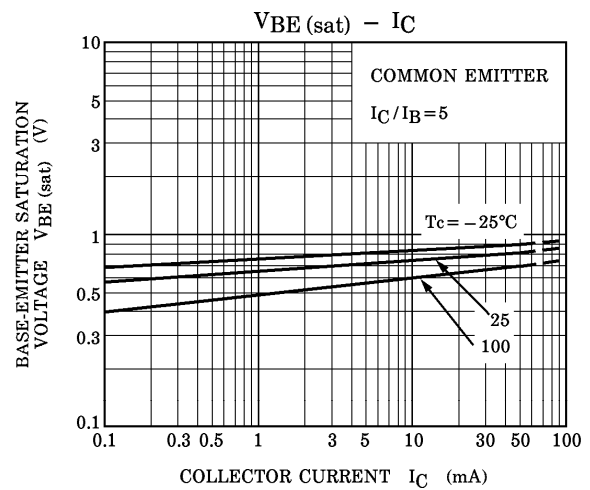
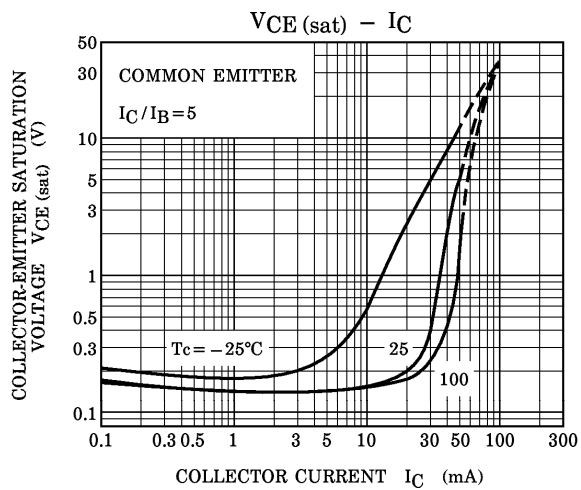
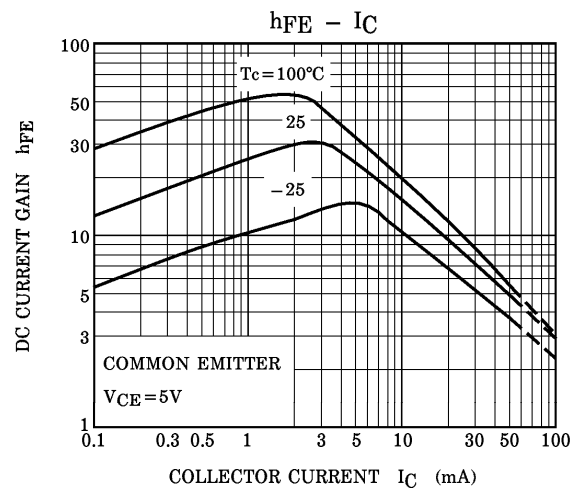
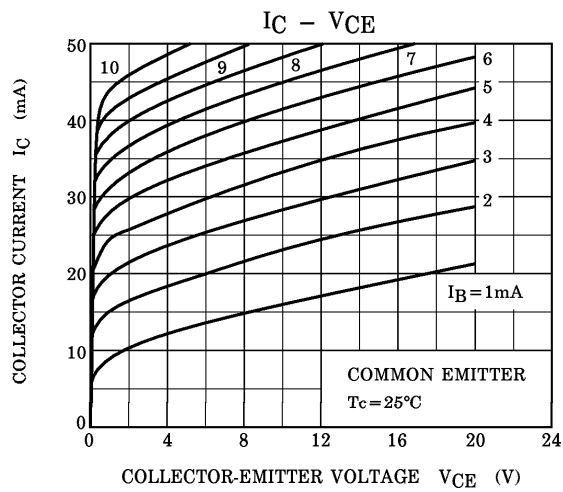
- High Voltage :  $V_{CEO} = 1200V$  (Max.)
- Small Collector Output Capacitance :  $C_{ob} = 2.2pF$  (Typ.)  
( $V_{CB} = 100V$ )

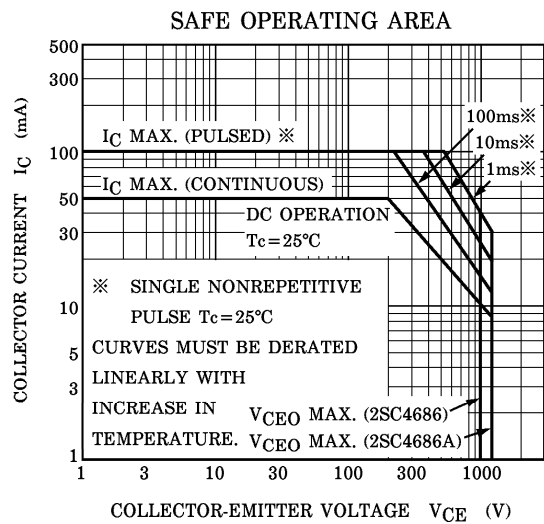
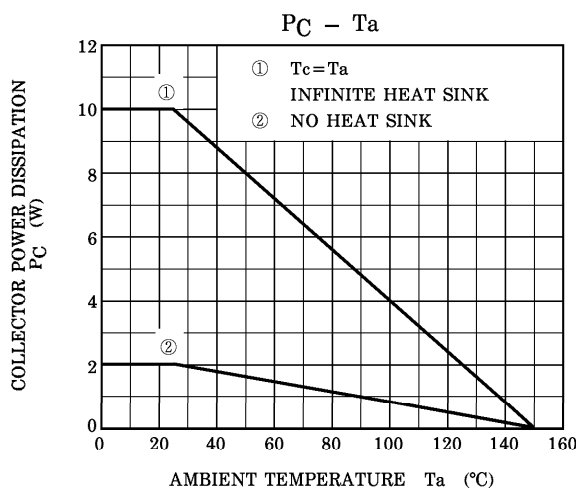
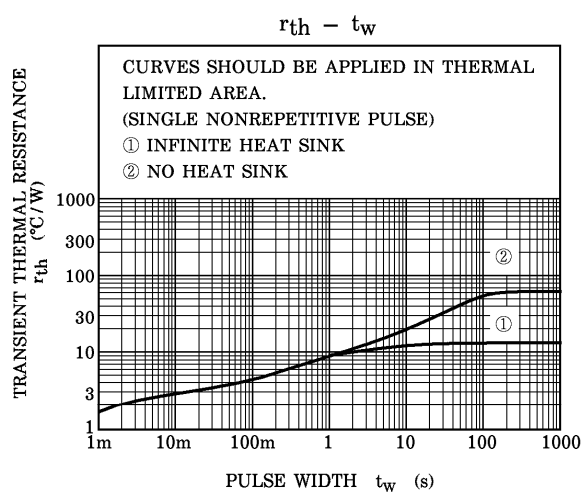
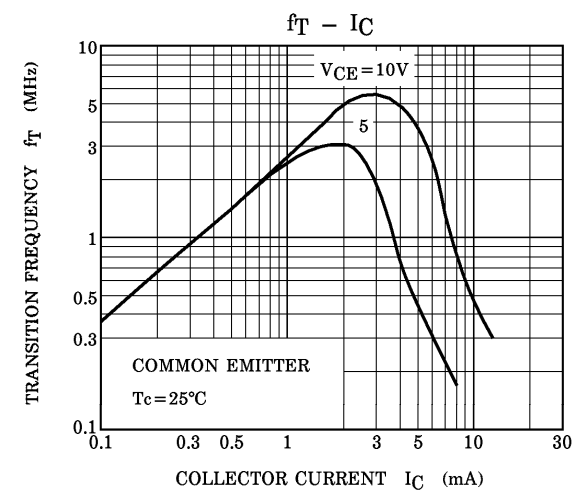
MAXIMUM RATINGS ( $T_c = 25^\circ C$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		$V_{CBO}$	1500	V
Collector-Emitter Voltage	2SC4686	$V_{CEO}$	1000	V
	2SC4686A		1200	
Emitter-Base Voltage		$V_{EBO}$	5	V
Collector Current	DC	$I_C$	50	mA
	Pulse	$I_{CP}$	100	
Base Current		$I_B$	25	mA
Collector Power Dissipation	$T_c = 25^\circ C$	$P_C$	10	W
	$T_a = 25^\circ C$		2	
Junction Temperature		$T_j$	150	$^\circ C$
Storage Temperature Range		$T_{stg}$	-55~150	$^\circ C$

ELECTRICAL CHARACTERISTICS ( $T_c = 25^\circ C$ )

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		$I_{CBO}$	$V_{CB} = 1200V, I_E = 0$	—	—	1.0	$\mu A$
Emitter Cut-off Current		$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	—	—	10	$\mu A$
Collector-Base Breakdown Voltage		$V_{(BR) CBO}$	$I_C = 100\mu A, I_E = 0$	1500	—	—	V
Collector-Emitter Breakdown Voltage	2SC4686	$V_{(BR) CEO}$	$I_C = 1mA, I_B = 0$	1000	—	—	V
	2SC4686A			1200	—	—	
DC Current Gain		$h_{FE}$	$V_{CE} = 5V, I_C = 3mA$	15	—	60	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 10mA, I_B = 2mA$	—	0.16	1.5	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 10mA, I_B = 2mA$	—	0.7	1.5	V
Transition Frequency		$f_T$	$V_{CE} = 10V, I_C = 3mA$	—	5.5	—	MHz
Collector Output Capacitance		$C_{ob}$	$V_{CB} = 100V, f = 1MHz, I_E = 0$	—	2.2	—	pF





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